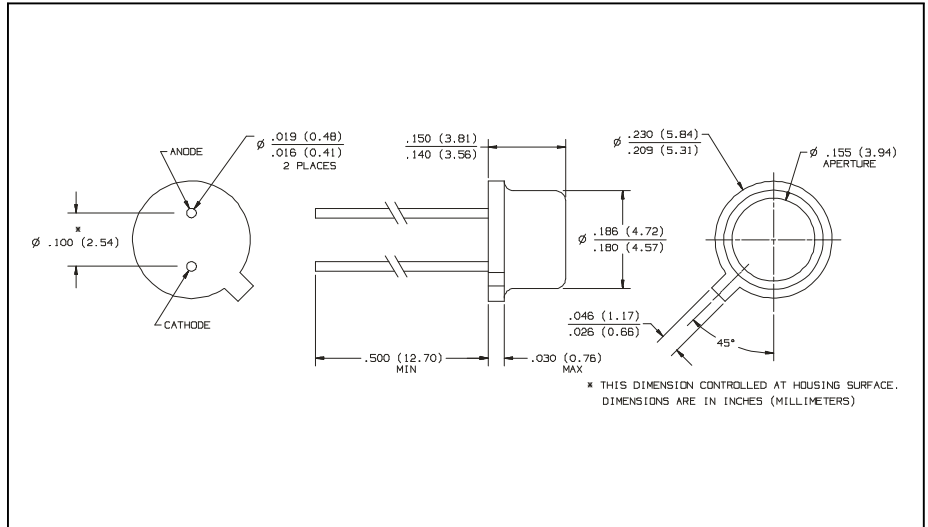


Hermetic Point Source Infrared Emitting Diode Type OP230WPS



Features

- Point source irradiance pattern
- Wavelength matched to silicon's peak response
- Fast switching speed
- TO-46 package style with flat window

Description

The OP230WPS is an 850 nm, top surface emitting, IRED. The .004" emitting area centered under a nondistorting flat lens can be used in many applications where external lensing is desired.

The stable V_F vs. Temperature characteristic make them ideal for applications where voltage is limited (such as battery operation).

The low t_r/t_f make them ideal for high speed operations.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| | |
|--|---|
| Reverse Voltage | 2.0 V |
| Continuous Forward Current | 100 mA |
| Peak Forward Current (2 μs pulse width, 0.1% duty cycle) | 1.0 A |
| Storage and Operating Temperature Range | -55 $^\circ\text{C}$ to +125 $^\circ\text{C}$ |
| Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron] | 260 $^\circ\text{C}$ ⁽¹⁾ |
| Power Dissipation | 200 mW ⁽²⁾ |

NOTES:

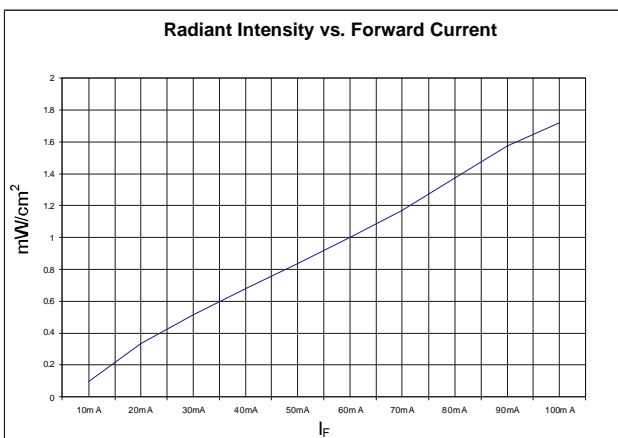
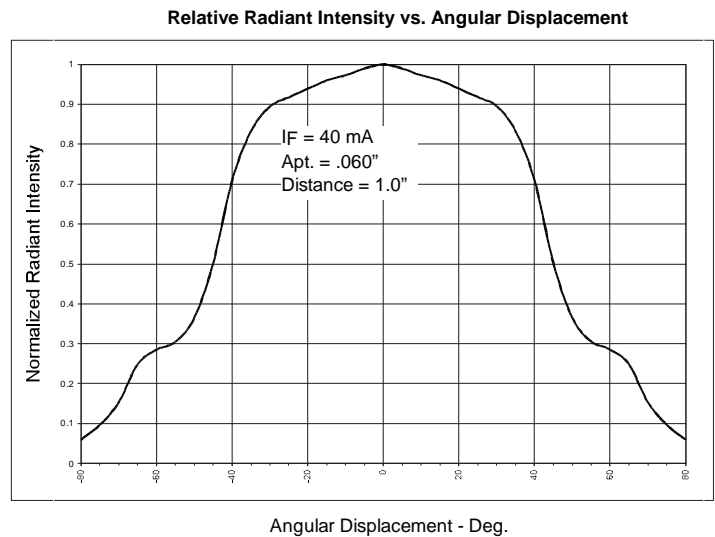
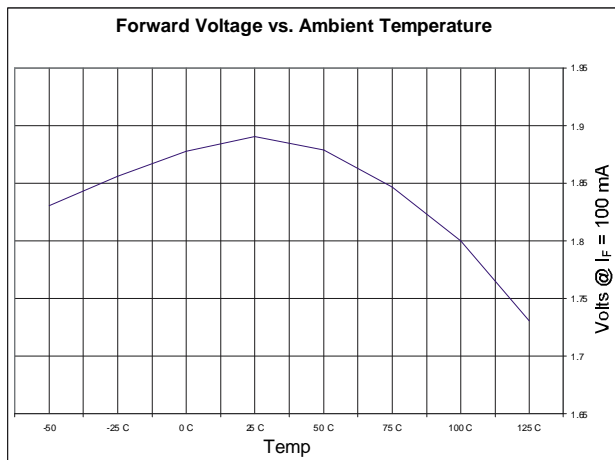
- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 2.0mW/ $^\circ\text{C}$ above 25 $^\circ\text{C}$.
- (3) $E_{e(\text{APT})}$ is a measurement of the average apertured radiant incidence upon a sensing area .250" (6.35 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and .466" (11.84 mm) from the measurement surface. $E_{e(\text{APT})}$ is not necessarily uniform within the measured area.

Type OP230WPS

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
|----------------------|--|-----|----------------|------|-------------------------|--|
| $E_{e(\text{APT})}$ | Apertured Irradiance | .5 | | | mW/cm^2 | $I_F = 100\text{ mA}$ |
| V_F | Forward Voltage | | | 2.20 | V | $I_F = 100\text{ mA}$ |
| I_R | Reverse Current | | | 1.0 | μA | $V_R = 2\text{ V}$ |
| λ_p | Wavelength Peak Emission | | 850 | | nm | $I_F = 100\text{ mA}$ |
| B | Spectral Bandwidth Between Half Power Points | | 80 | | nm | $I_F = 100\text{ mA}$ |
| θ_{HP} | Emission Angle at Half Power Points | | $\pm 45^\circ$ | | Deg. | $I_F = 100\text{ mA}$ |
| t_r | Rise Time | | 10 | | ns | $I_{F(\text{PK})} = 100\text{ mA}$ |
| t_f | Fall Time | | 10 | | ns | $\text{PW} = 10\ \mu\text{s}$, D.C. = 10% |

Typical Performance Curves



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

Optek Technology, Inc. 1215 W. Crosby Road Carrollton, Texas 75006 (972)323-2200 Fax (972)323-2396